

### KSE170/171/172

Low Power Audio Amplifier Low Current, High Speed Switching Applications



## **PNP Epitaxial Silicon Transistor**

### **Absolute Maximum Ratings** T<sub>C</sub>=25°C unless otherwise noted

Symbol	Parameter		Value	Units	
$V_{CBO}$	Collector-Base Voltage	: KSE170	- 60	V	
020		: KSE171	- 80	V	
		: KSE172	- 100	V	
V <sub>CEO</sub>	Collector-Emitter Voltage	: KSE170	- 40	V	
		: KSE171	- 60	V	
		: KSE172	- 80	V	
V <sub>EBO</sub>	Emitter-Base Voltage		- 7	V	
I <sub>C</sub>	Collector Current (DC)		- 3	А	
I <sub>CP</sub>	Collector Current (Pulse)		- 6	Α	
I <sub>B</sub>	Base Current		- 1	А	
P <sub>C</sub>	Collector Dissipation (T <sub>C</sub> =25°C)		12.5	W	
	Collector Dissipation (T <sub>a</sub> =25°C)		1.5	W	
T <sub>J</sub>	Junction Temperature		150	°C	
T <sub>STG</sub>	Storage Temperature		- 65 ~ 150	°C	

### Electrical Characteristics T<sub>C</sub>=25°C unless otherwise noted

Symbol	Parameter	Test Condition	Min.	Max.	Units
BV <sub>CEO</sub>	Collector-Emitter Breaksown Voltage : KSE170 : KSE171 : KSE172	I <sub>C</sub> = 10mA, I <sub>B</sub> = 0	-40 -60 -80		V V V
Ісво	Collector Cut-off Current : KSE170 : KSE171 : KSE172 : KSE170 : KSE171 : KSE172	$\begin{split} &V_{CB} = -60V,  I_B = 0 \\ &V_{CB} = -80V,  I_E = 0 \\ &V_{CB} = -100V,  I_E = 0 \\ &V_{CB} = -60V,  I_E = 0,  T_C = 150^{\circ}C \\ &V_{CB} = -80V,  I_E = 0,  T_C = 150^{\circ}C \\ &V_{CB} = -100V,  I_E = 0,  T_C = 150^{\circ}C \end{split}$		-0.1 -0.1 -0.1 -0.1 -0.1	μΑ μΑ μΑ mA mA
I <sub>EBO</sub>	Emitter Cut-off Current	$V_{BE} = -7V, I_{C} = 0$		-0.1	μΑ
h <sub>FE</sub>	DC Current Gain	$V_{CE} = -1V$ , $I_{C} = -100mA$ $V_{CE} = -1V$ , $I_{C} = -500mA$ $V_{CE} = -1V$ , $I_{C} = -1.5A$	50 30 12	250	
V <sub>CE</sub> (sat)	Collector-Emitter Saturation Voltage	$I_C = -500$ mA, $I_B = -50$ mA $I_C = -1.5$ A, $I_B = -150$ mA $I_C = -3$ A, $I_B = -600$ mA		-0.3 -0.9 -1.7	V V V
V <sub>BE</sub> (sat)	Base-Emitter Saturation Voltage	I <sub>C</sub> = - 1.5A, I <sub>B</sub> = - 150mA I <sub>C</sub> = - 3A, I <sub>B</sub> = - 600mA		-1.5 -2.0	V V
V <sub>BE</sub> (on)	Base-Emitter On Voltage	V <sub>CE</sub> = - 1V, I <sub>C</sub> = - 500mA		-1.2	V
f <sub>T</sub>	Current Gain Bandwidth Product	V <sub>CE</sub> = - 10V, I <sub>C</sub> = - 100mA	50		MHz
C <sub>ob</sub>	Output Capacitance	$V_{CB} = -10V, I_E = 0, f = 0.1MHz$		50	pF

## **Typical Charactristics**

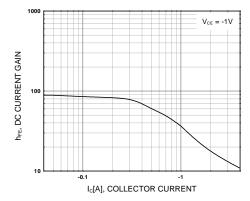


Figure 1. DC current Gain

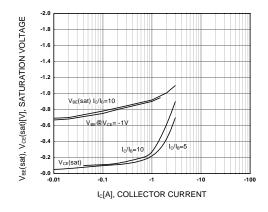


Figure 2. Base-Emitter Saturation Voltage Collector-Emitter Saturation Voltage

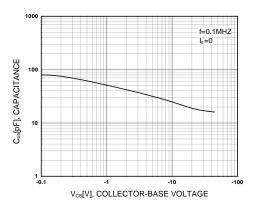


Figure 3. Collector Output Capacitance

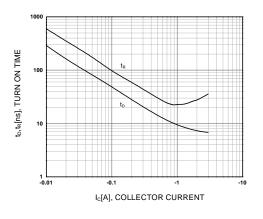


Figure 4. Turn On Time

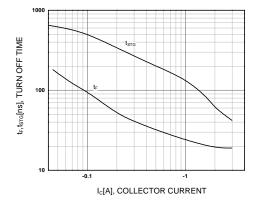


Figure 5. Turn Off Time

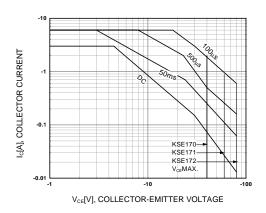


Figure 6. Safe Operating Area

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# Typical Characteristics (Continued)

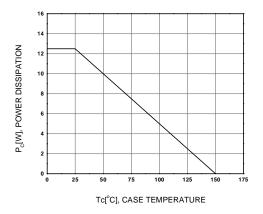
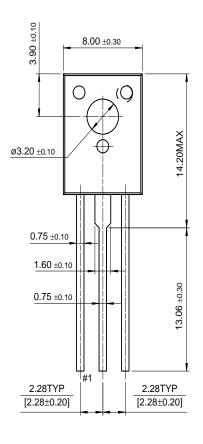
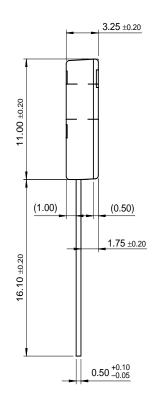


Figure 7. DC current Gain

## **Package Demensions**

TO-126







Dimensions in Millimeters

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